

CLAIMS

1. A bipolar transistor, comprising:
 - a first semiconductor region of a first conductivity type defining a collector region;
 - a second semiconductor region of a second conductivity type defining a base region;
 - a third semiconductor region of said first conductivity type defining a emitter region; and
 - a metal layer providing contacts to said base and emitter regions;
wherein the transistor has a specific area resistance less than about 500mOhms.mm²; and
wherein said metal layer has a thickness greater than about 3μm.
2. A bipolar transistor according to claim 1, wherein the metal layer has a thickness no less than 4μm.
3. A bipolar transistor according to any preceding claim, wherein the metal layer has a thickness no less than 6μm.
4. A bipolar transistor according to any preceding claim, wherein the emitter region defines a first surface, the base region extending to said surface in locations defined by apertures through emitter region, said metal layer overlying said first surface.
5. A bipolar transistor according to claim 4, wherein adjacent apertures are spaced less than 100μm from each other.
6. A bipolar transistor substantially as hereinbefore defined, with reference to the accompanying drawing.